

## DESCRIPTION

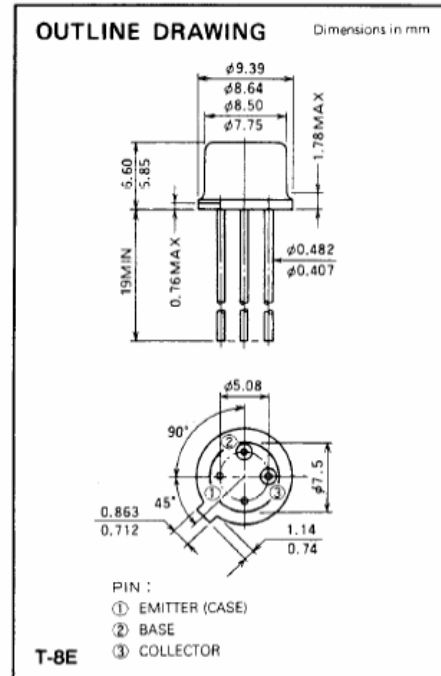
2SC3101 is a silicon NPN epitaxial planar type transistor specifically designed for UHF power amplifiers applications.

## FEATURES

- High power gain:  $G_{pe} \geq 5.7\text{dB}$   
@ $V_{CC} = 12.5\text{V}$ ,  $f = 520\text{MHz}$ ,  $P_{in} = 0.8\text{W}$
- Emitter ballasted construction
- High ruggedness: Ability to withstand more than 20:1 load VSWR when operated at @ $V_{CC} = 15.2\text{V}$ ,  $f = 520\text{MHz}$ ,  $P_O = 3\text{W}$ .

## APPLICATION

For drive stage and output stage of power amplifiers in UHF band.



## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CEO}$	Collector to base voltage		35	V
$V_{EBO}$	Emitter to base voltage		4	V
$V_{CEO}$	Collector to emitter voltage	$R_{BE} = \infty$	17	V
$I_C$	Collector current		1	A
$P_C$	Collector dissipation	$T_C = 25^\circ\text{C}$	10	W
$T_J$	Junction temperature		175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55 to 175	$^\circ\text{C}$

Note: Above parameters are guaranteed independently.

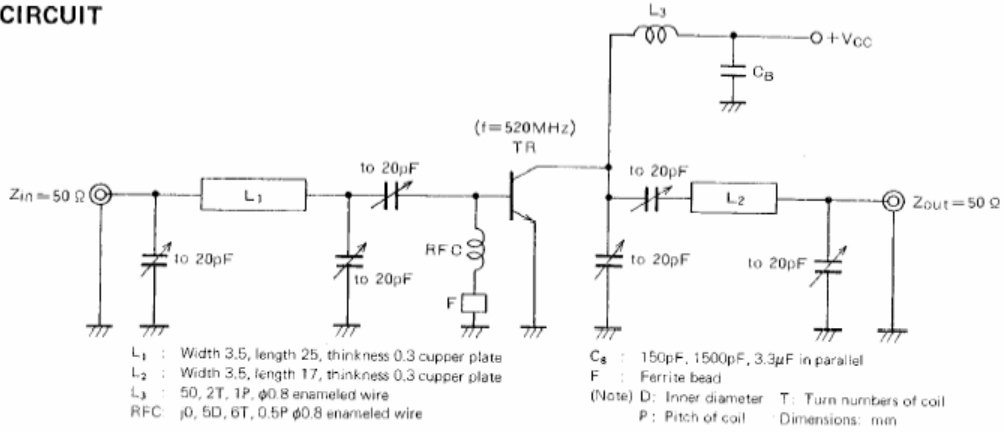
## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 1\text{mA}$ , $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$ , $I_E = 0$	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 10\text{mA}$ , $R_{BE} = \infty$	17			V
$I_{CBO}$	Collector cutoff current	$V_{CB} = 15\text{V}$ , $I_E = 0$			300	$\mu\text{A}$
$I_{EBO}$	Emitter cutoff current	$V_{EB} = 2\text{V}$ , $I_C = 0$			300	$\mu\text{A}$
$h_{FE}$	DC forward current gain *	$V_{CB} = 10\text{V}$ , $I_C = 0.1\text{A}$	10	50	180	—
$P_O$	Output power	$V_{CC} = 12.5\text{V}$ , $P_{in} = 0.8\text{W}$ , $f = 520\text{MHz}$ .	3	3.5		W
$\eta_C$	Collector efficiency		50	60		%

Note: \* Pulse test,  $P_W = 150\mu\text{s}$ , duty = 5%.

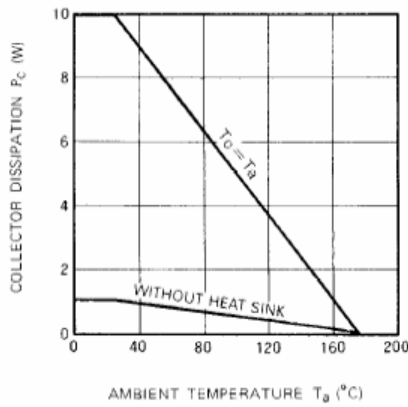
Above parameters, ratings, limits and conditions are subject to change.

## TEST CIRCUIT

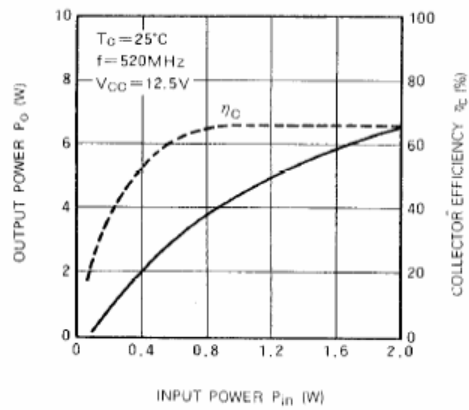


## TYPICAL PERFORMANCE DATA

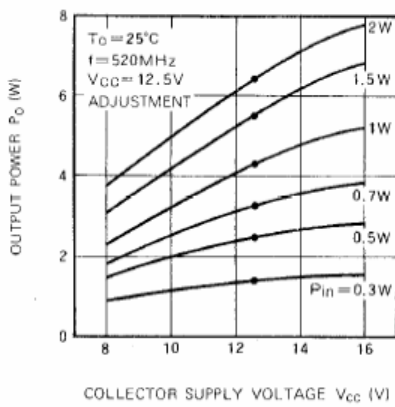
**COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE CHARACTERISTICS**



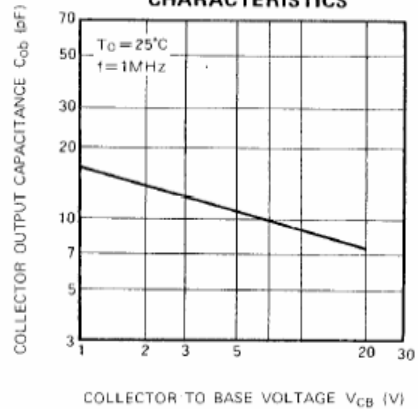
**OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER CHARACTERISTICS**



**OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE CHARACTERISTICS**



**COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE CHARACTERISTICS**





**Sales Offices**

<p><b>CHINA</b></p> <p><b>ELEFLOW TECHNOLOGIES(HQ)</b> Suite1-603, HuaKang Plaza 109 ZhenXing Road, Futian District ShenZhen518031, P.R. China Phone: 86-755-83204665/83204663 Fax: 86-755-8320 4659 Email: eleflow@163.com</p> <p><b>USA</b></p> <p><b>ELEFLOW TECHNOLOGIES(USA)</b> Mr. Ted Seymore (Manager) 3291 NE 4th Ave., Boca Raton Florida 33431-6011, USA Phone: 561-302-7007 Fax: 561- 852-0505 Email: tedseymour@adelphia.net</p>	<p><b>R &amp; D CENTER</b></p> <p><b>ELEFLOW TECHNOLOGIES(R&amp;D CENTER)</b> Overseas Chinese High-Tech Venture Park No. 12 South, Hi-tech Park, NanShan Dist. ShenZhen518057, China</p>
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